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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re the Application of: **H. WATANABE et al.**

Serial No.: **09/320,271**

Group Art Unit: **2825**

Filed: **May 27, 1999**

Examiner: **C. Lee**

For: **SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREOF**

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Date: May 14, 2001

Sir:

Prior to continued examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) A fabrication method of a semiconductor device comprising the steps of:
- forming a first insulation layer over a substrate,
- introducing impurities into said first insulation layer, and
- embedding and forming a first conductive layer in said first insulation layer.

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